

N-channel 250 V, 318 mΩ, 8 A STripFET™ II Power MOSFET in DPAK package

Datasheet — production data

Features

Order code	V _{DSS}	R _{DS(on)} max.	I _D
STD8NF25	250 V	< 420 mΩ	8 A

- 100% avalanche tested
- 175 °C junction temperature

Applications

- Switching applications
 - Automotive

Description

This Power MOSFET has been developed using STMicroelectronics' unique STripFET process, which is specifically designed to minimize input capacitance and gate charge. This renders the device suitable for use as primary switch in advanced high-efficiency isolated DC-DC converters for telecom and computer applications, and applications with low gate charge driving requirements.

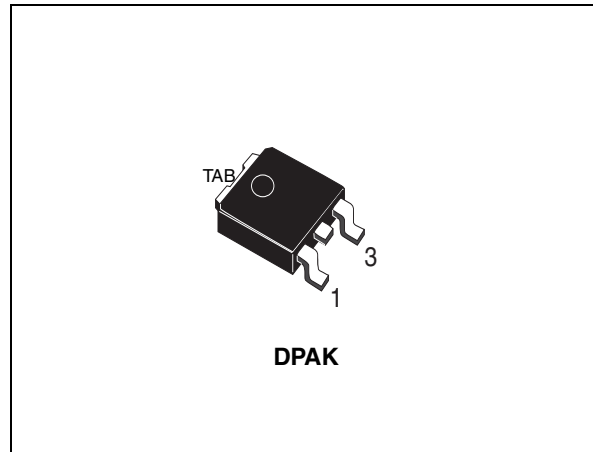


Figure 1. Internal schematic diagram

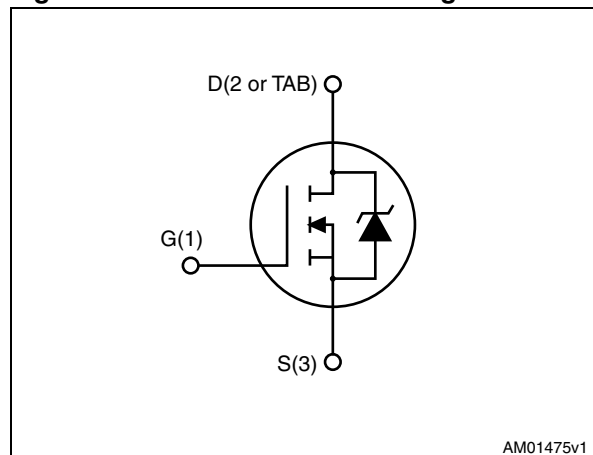


Table 1. Device summary

Order code	Marking	Package	Packaging
STD8NF25	8NF25	DPAK	Tape and reel

Contents

1	Electrical ratings	3
2	Electrical characteristics	4
	2.1 Electrical characteristics (curves)	6
3	Test circuits	8
4	Package mechanical data	9
5	Packaging mechanical data	11
6	Revision history	13

1 Electrical ratings

Table 2. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{DS}	Drain-source voltage	250	V
V_{GS}	Gate-source voltage	± 20	V
$I_D^{(1)}$	Drain current (continuous) at $T_C = 25\text{ }^\circ\text{C}$	8	A
	Drain current (continuous) at $T_C = 100\text{ }^\circ\text{C}$	6	A
$I_{DM}^{(2)}$	Drain current (pulsed)	32	A
P_{TOT}	Total dissipation at $T_C = 25\text{ }^\circ\text{C}$	72	W
T_J T_{stg}	Operating junction temperature Storage temperature	-55 to 175	$^\circ\text{C}$

1. The value is rated according to R_{thj-c} .

2. Pulse is rated according to SOA.

Table 3. Thermal data

Symbol	Parameter	Value	Unit
$R_{thj-case}$	Thermal resistance junction-case	2.08	$^\circ\text{C/W}$
$R_{thj-pcb}^{(1)}$	Thermal resistance junction-pcb	50	

1. When mounted on 1inch² FR-4, 2 Oz copper board.

Table 4. Avalanche data

Symbol	Parameter	Value	Unit
I_{AV}	Non-repetitive avalanche current	8	A
E_{AS}	Single pulse avalanche energy (starting $T_J = 25\text{ }^\circ\text{C}$, $I_D = I_{AV}$, $V_{DD} = 50\text{ V}$)	110	mJ

2 Electrical characteristics

($T_{CASE}=25\text{ °C}$ unless otherwise specified).

Table 5. On/off states

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	$I_D = 1\text{ mA}, V_{GS} = 0$	250	-		V
I_{DSS}	Zero gate voltage drain current ($V_{GS} = 0$)	$V_{DS} = 250\text{ V}$ $V_{DS} = 250\text{ V}, T_c = 125\text{ °C}$		-	1 50	μA μA
I_{GSS}	Gate body leakage current ($V_{DS} = 0$)	$V_{GS} = \pm 20\text{ V}$		-	± 100	nA
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	2	-	4	V
$R_{DS(on)}$	Static drain-source on-resistance	$V_{GS} = 10\text{ V}, I_D = 8\text{ A}$		318	420	m Ω

Table 6. Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
C_{iss}	Input capacitance	$V_{DS} = 25\text{ V}, f = 1\text{ MHz}, V_{GS} = 0$		500		pF
C_{oss}	Output capacitance		-	90	-	pF
C_{rss}	Reverse transfer capacitance			15		pF
Q_g	Total gate charge	$V_{DD} = 200\text{ V}, I_D = 8\text{ A}$		16		nC
Q_{gs}	Gate-source charge	$V_{GS} = 10\text{ V}$	-	3.5	-	nC
Q_{gd}	Gate-drain charge	(see Figure 14)		8		nC

Table 7. Switching times

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	$V_{DD} = 125\text{ V}, I_D = 4\text{ A},$ $R_G = 4.7\text{ }\Omega, V_{GS} = 10\text{ V}$ (see Figure 13 and Figure 18)		13		ns
t_r	Rise time		-	10	-	ns
$t_{d(off)}$	Turn-off delay time			26		ns
t_f	Fall time		-	6	-	ns

Table 8. Source drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
I_{SD} I_{SDM}	Source-drain current Source-drain current (pulsed)		-		8 32	A A
V_{SD}	Forward on voltage	$I_{SD}=8\text{ A}$, $V_{GS}=0\text{ V}$	-		1.5	V
t_{rr} Q_{rr} I_{RRM}	Reverse recovery time Reverse recovery charge Reverse recovery current	$I_{SD} = 8\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$, $V_{DD} = 50\text{ V}$ (see Figure 15)	-	115 470 8.5		ns nC A
t_{rr} Q_{rr} I_{RRM}	Reverse recovery time Reverse recovery charge Reverse recovery current	$I_{SD} = 8\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$, $V_{DD} = 50\text{ V}$, $T_J = 150\text{ }^\circ\text{C}$ (see Figure 15)	-	130 580 9.5		ns nC A

2.1 Electrical characteristics (curves)

Figure 2. Safe operating area

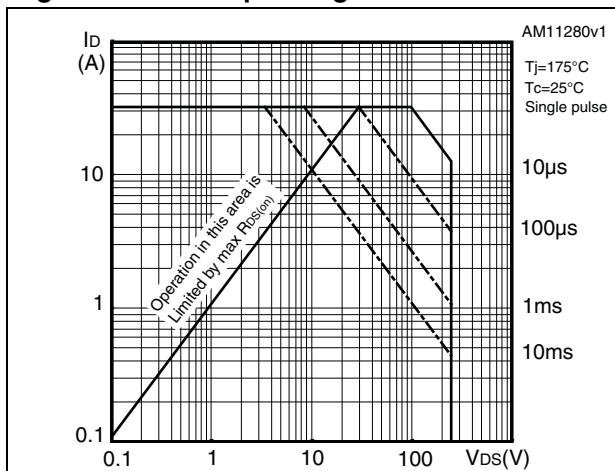


Figure 3. Thermal impedance

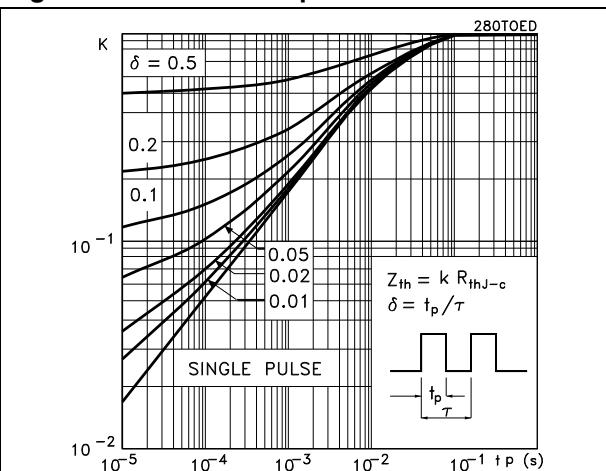


Figure 4. Output characteristics

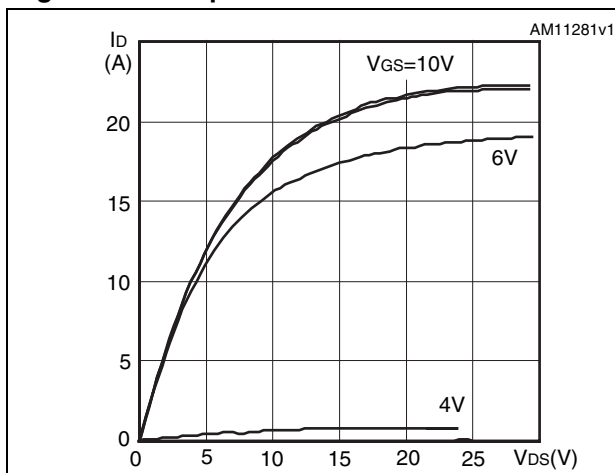


Figure 5. Transfer characteristics

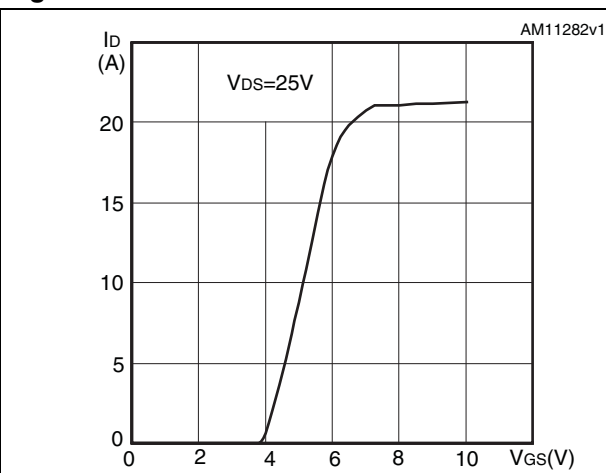


Figure 6. Normalized BV_{DSS} vs temperature

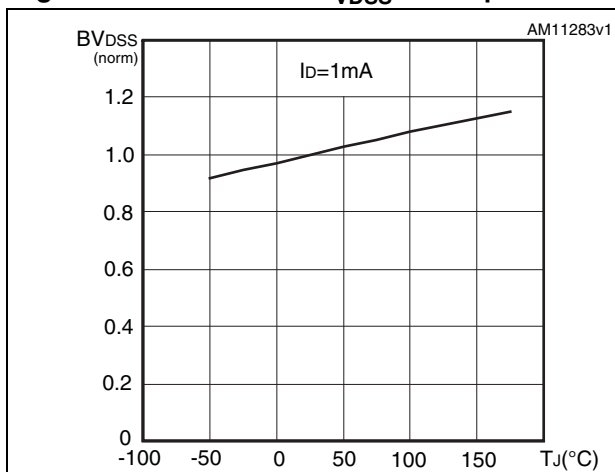


Figure 7. Static drain-source on-resistance

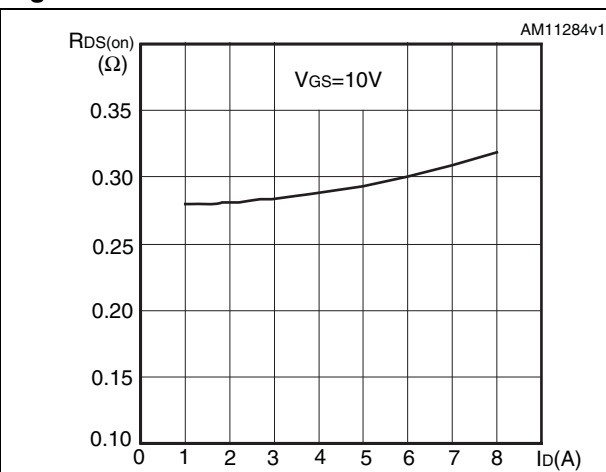


Figure 8. Gate charge vs gate-source voltage Figure 9. Capacitance variations

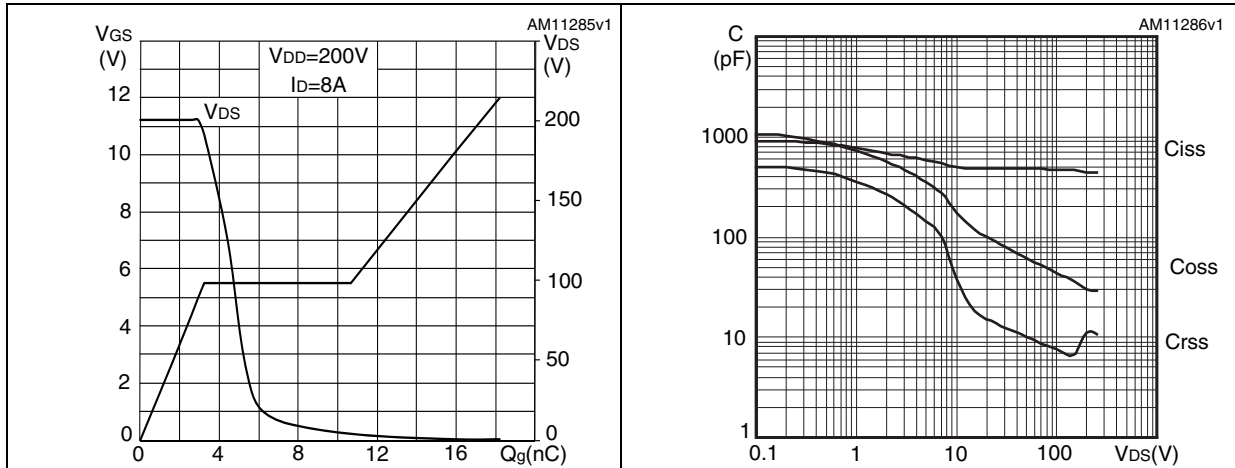


Figure 10. Normalized gate threshold voltage vs temperature Figure 11. Normalized on resistance vs temperature

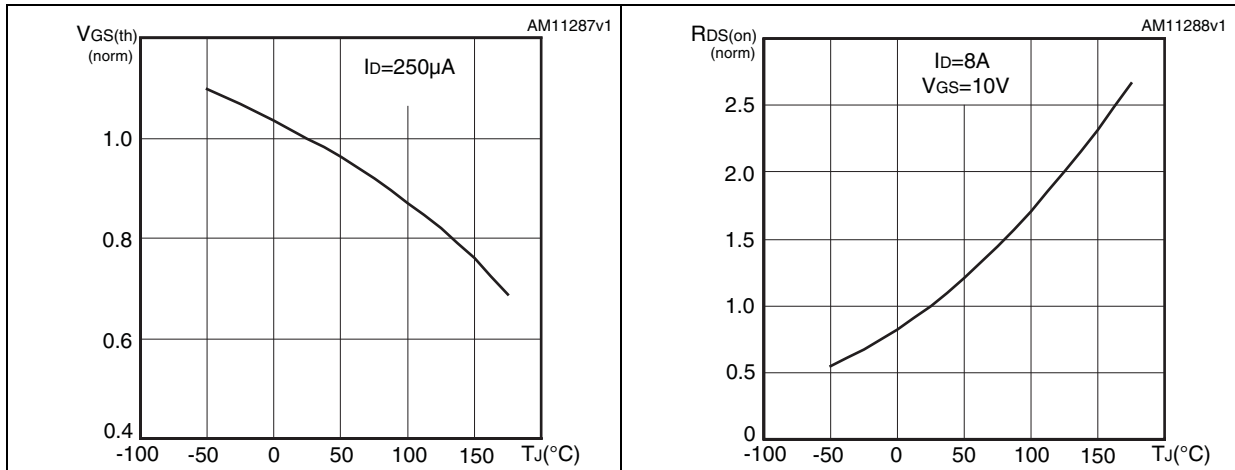
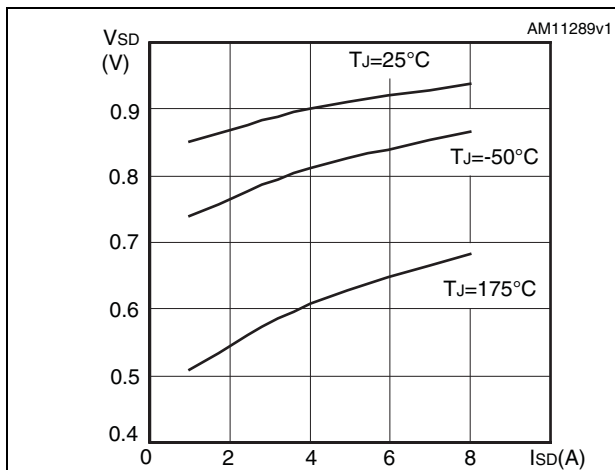


Figure 12. Source-drain diode forward characteristics



3 Test circuits

Figure 13. Switching times test circuit for resistive load



Figure 14. Gate charge test circuit

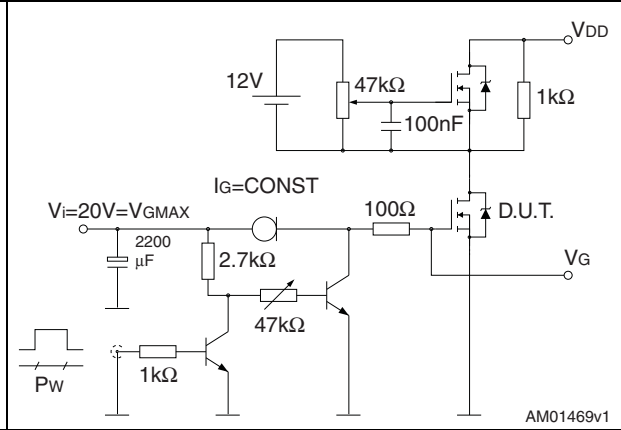


Figure 15. Test circuit for inductive load switching and diode recovery times



Figure 16. Unclamped inductive load test circuit



Figure 17. Unclamped inductive waveform

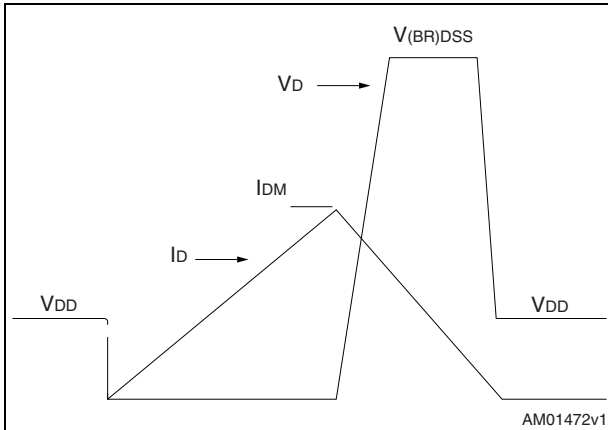
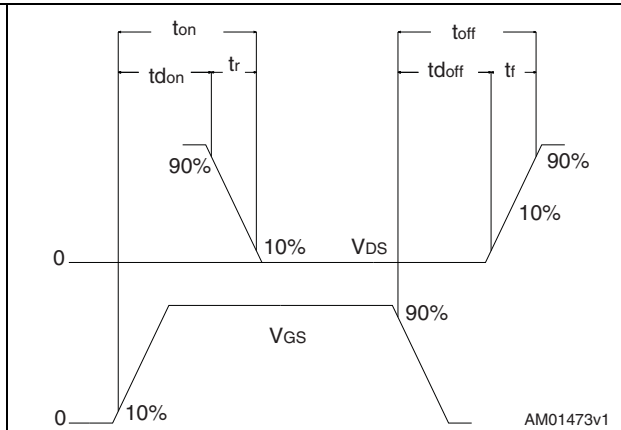


Figure 18. Switching time waveform



4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK specifications, grade definitions and product status are available at: www.st.com. ECOPACK is an ST trademark.

Table 9. DPAK (TO-252) mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	2.20		2.40
A1	0.90		1.10
A2	0.03		0.23
b	0.64		0.90
b4	5.20		5.40
c	0.45		0.60
c2	0.48		0.60
D	6.00		6.20
D1		5.10	
E	6.40		6.60
E1		4.70	
e		2.28	
e1	4.40		4.60
H	9.35		10.10
L	1		1.50
L1		2.80	
L2		0.80	
L4	0.60		1
R		0.20	
V2	0°		8°

Figure 19. DPAK (TO-252) drawing

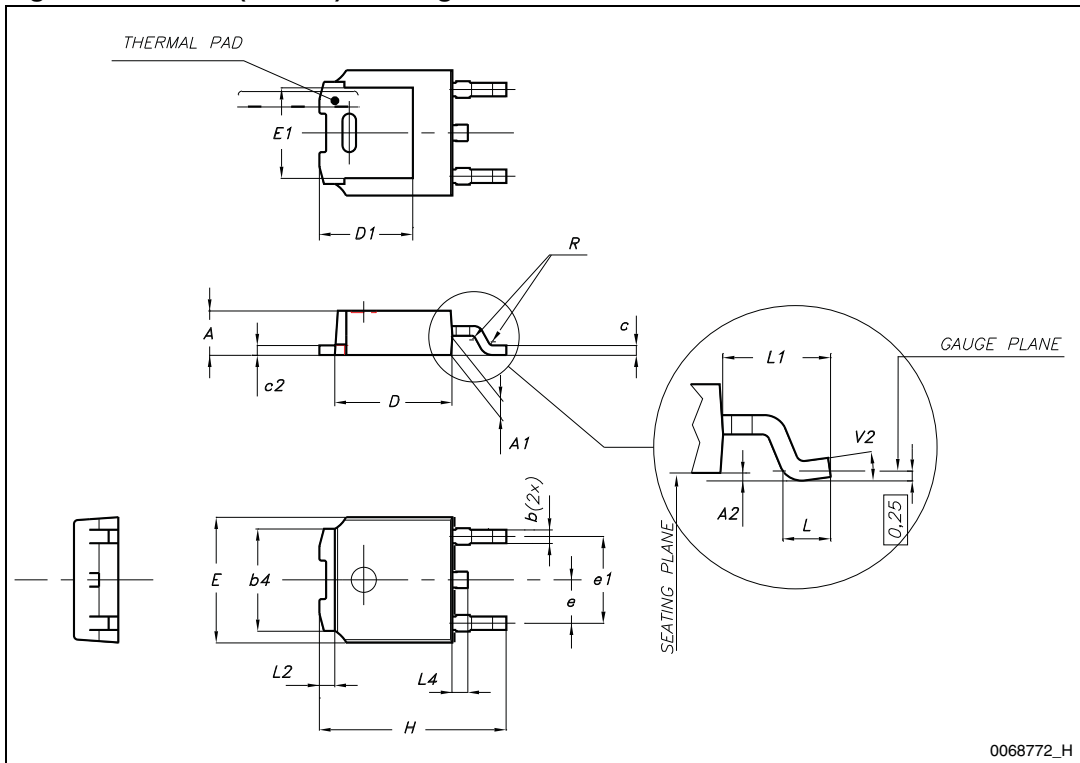
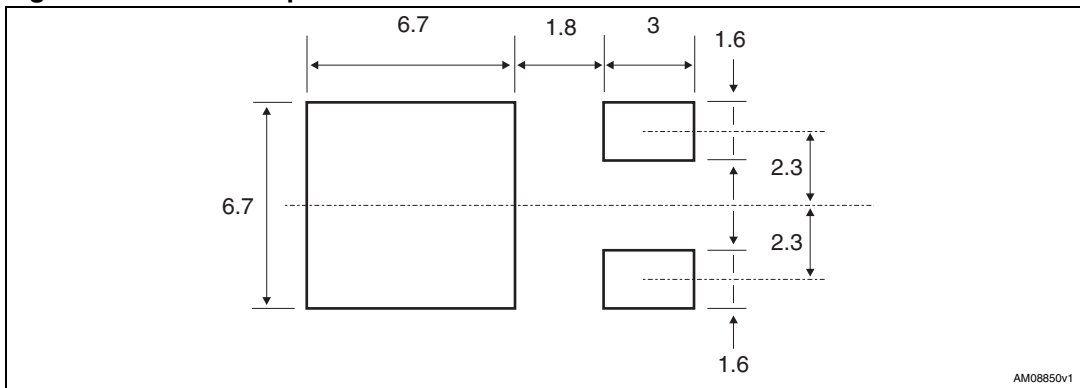


Figure 20. DPAK footprint^(a)



a. All dimensions are in millimeters.

5 Packaging mechanical data

Table 10. DPAK (TO-252) tape and reel mechanical data

Tape			Reel		
Dim.	mm		Dim.	mm	
	Min.	Max.		Min.	Max.
A0	6.8	7	A		330
B0	10.4	10.6	B	1.5	
B1		12.1	C	12.8	13.2
D	1.5	1.6	D	20.2	
D1	1.5		G	16.4	18.4
E	1.65	1.85	N	50	
F	7.4	7.6	T		22.4
K0	2.55	2.75			
P0	3.9	4.1	Base qty.		2500
P1	7.9	8.1	Bulk qty.		2500
P2	1.9	2.1			
R	40				
T	0.25	0.35			
W	15.7	16.3			

Figure 21. Tape for DPAK (TO-252)

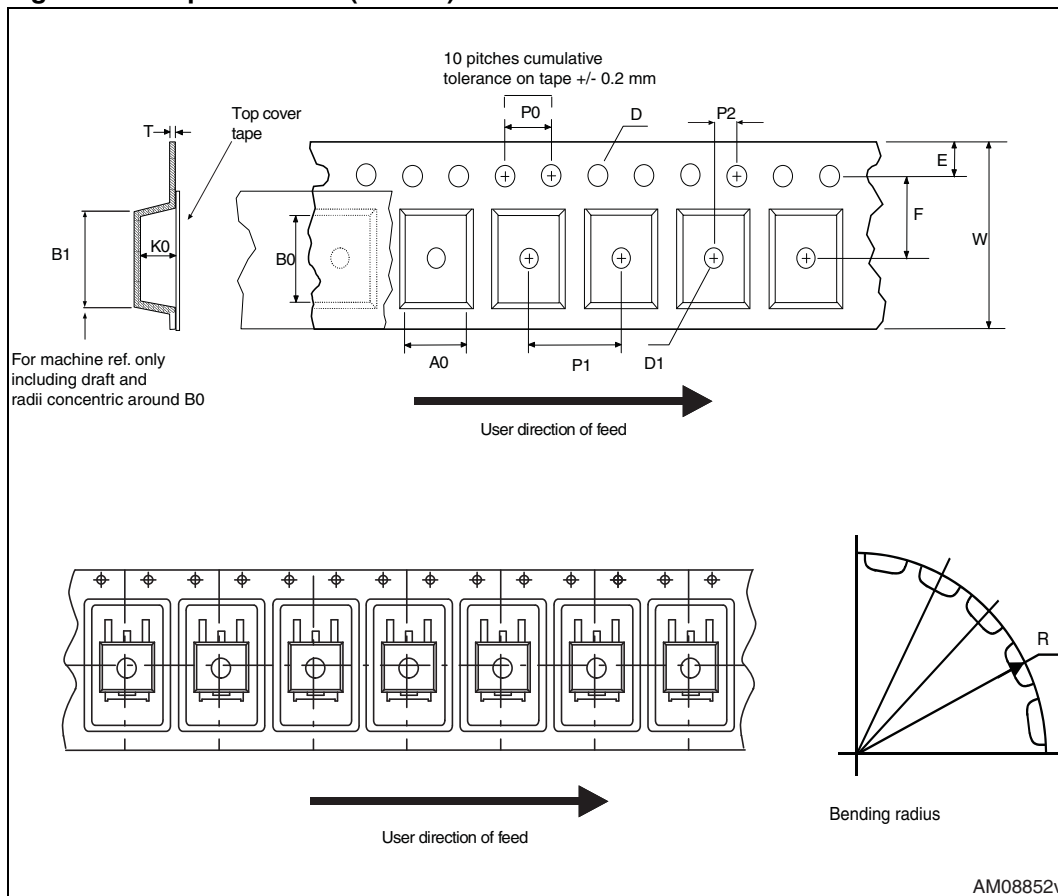
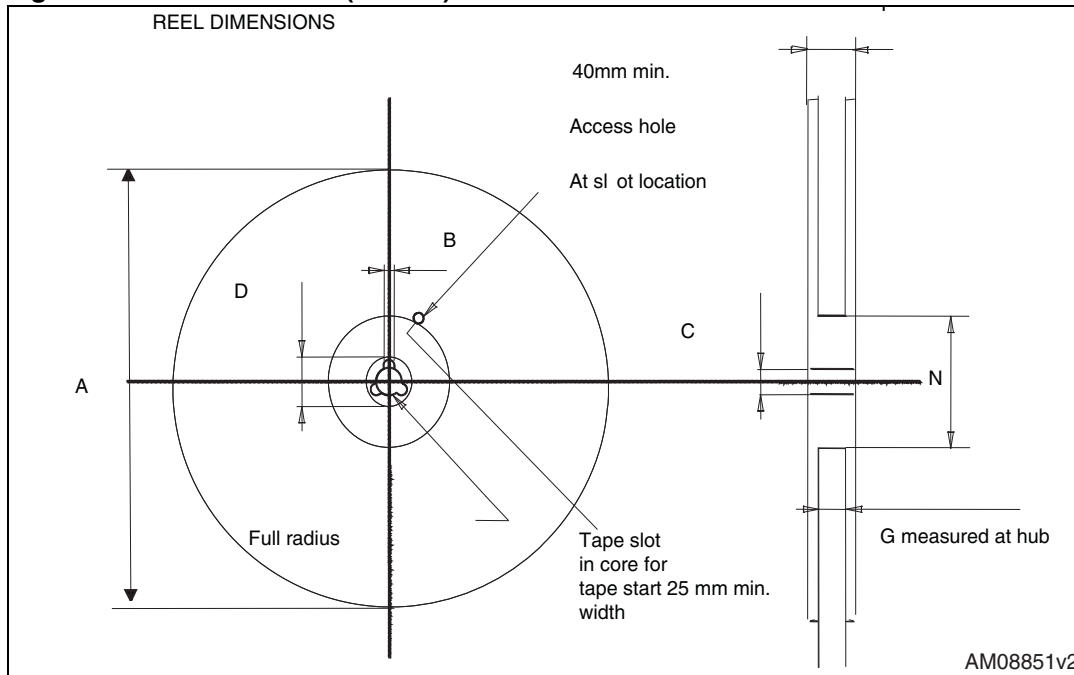


Figure 22. Reel for DPAK (TO-252)



6 Revision history

Table 11. Document revision history

Date	Revision	Changes
26-Apr-2012	1	First release.

Please Read Carefully:

Information in this document is provided solely in connection with ST products. STMicroelectronics NV and its subsidiaries ("ST") reserve the right to make changes, corrections, modifications or improvements, to this document, and the products and services described herein at any time, without notice.

All ST products are sold pursuant to ST's terms and conditions of sale.

Purchasers are solely responsible for the choice, selection and use of the ST products and services described herein, and ST assumes no liability whatsoever relating to the choice, selection or use of the ST products and services described herein.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted under this document. If any part of this document refers to any third party products or services it shall not be deemed a license grant by ST for the use of such third party products or services, or any intellectual property contained therein or considered as a warranty covering the use in any manner whatsoever of such third party products or services or any intellectual property contained therein.

UNLESS OTHERWISE SET FORTH IN ST'S TERMS AND CONDITIONS OF SALE ST DISCLAIMS ANY EXPRESS OR IMPLIED WARRANTY WITH RESPECT TO THE USE AND/OR SALE OF ST PRODUCTS INCLUDING WITHOUT LIMITATION IMPLIED WARRANTIES OF MERCHANTABILITY, FITNESS FOR A PARTICULAR PURPOSE (AND THEIR EQUIVALENTS UNDER THE LAWS OF ANY JURISDICTION), OR INFRINGEMENT OF ANY PATENT, COPYRIGHT OR OTHER INTELLECTUAL PROPERTY RIGHT.

UNLESS EXPRESSLY APPROVED IN WRITING BY TWO AUTHORIZED ST REPRESENTATIVES, ST PRODUCTS ARE NOT RECOMMENDED, AUTHORIZED OR WARRANTED FOR USE IN MILITARY, AIR CRAFT, SPACE, LIFE SAVING, OR LIFE SUSTAINING APPLICATIONS, NOR IN PRODUCTS OR SYSTEMS WHERE FAILURE OR MALFUNCTION MAY RESULT IN PERSONAL INJURY, DEATH, OR SEVERE PROPERTY OR ENVIRONMENTAL DAMAGE. ST PRODUCTS WHICH ARE NOT SPECIFIED AS "AUTOMOTIVE GRADE" MAY ONLY BE USED IN AUTOMOTIVE APPLICATIONS AT USER'S OWN RISK.

Resale of ST products with provisions different from the statements and/or technical features set forth in this document shall immediately void any warranty granted by ST for the ST product or service described herein and shall not create or extend in any manner whatsoever, any liability of ST.

ST and the ST logo are trademarks or registered trademarks of ST in various countries.

Information in this document supersedes and replaces all information previously supplied.

The ST logo is a registered trademark of STMicroelectronics. All other names are the property of their respective owners.

© 2012 STMicroelectronics - All rights reserved

STMicroelectronics group of companies

Australia - Belgium - Brazil - Canada - China - Czech Republic - Finland - France - Germany - Hong Kong - India - Israel - Italy - Japan - Malaysia - Malta - Morocco - Philippines - Singapore - Spain - Sweden - Switzerland - United Kingdom - United States of America

www.st.com